

# Voltage Regulator - Low Power Low, Dropout 100 mA

## LP2950, LP2951, NCV2951

The LP2950 and LP2951 are micropower voltage regulators that are specifically designed to maintain proper regulation with an extremely low input–to–output voltage differential. These devices feature a very low quiescent bias current of 75  $\mu A$  and are capable of supplying output currents in excess of 100 mA. Internal current and thermal limiting protection is provided.

The LP2951 has three additional features. The first is the Error Output that can be used to signal external circuitry of an out of regulation condition, or as a microprocessor power–on reset. The second feature allows the output voltage to be preset to 5.0 V, 3.3 V or 3.0 V output (depending on the version) or programmed from 1.25 V to 29 V. It consists of a pinned out resistor divider along with direct access to the Error Amplifier feedback input. The third feature is a Shutdown input that allows a logic level signal to turn–off or turn–on the regulator output.

Due to the low input-to-output voltage differential and bias current specifications, these devices are ideally suited for battery powered computer, consumer, and industrial equipment where an extension of useful battery life is desirable. The LP2950 is available in the three pin case 29 and DPAK packages, and the LP2951 is available in the eight pin dual-in-line, SOIC-8 and Micro8 surface mount packages. The 'A' suffix devices feature an initial output voltage tolerance  $\pm 0.5\%$ .

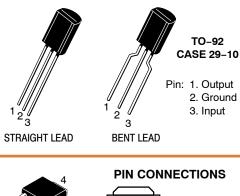
#### **Features**

- Low Quiescent Bias Current of 75 μA
- $\bullet\,$  Low Input–to–Output Voltage Differential of 50 mV at 100  $\mu A$  and 380 mV at 100 mA
- 5.0 V, 3.3 V or 3.0 V  $\pm 0.5\%$  Allows Use as a Regulator or Reference
- Extremely Tight Line and Load Regulation
- Requires Only a 1.0 µF Output Capacitor for Stability
- Internal Current and Thermal Limiting
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and RoHS Compliant

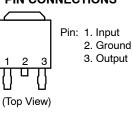
#### LP2951 Additional Features

- Error Output Signals an Out of Regulation Condition
- Output Programmable from 1.25 V to 29 V
- Logic Level Shutdown Input

(See Following Page for Device Information.)







Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.



SOIC-8 CASE 751

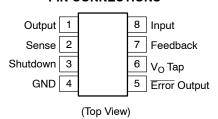






Micro8 CASE 846A

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on pages 14 and 15 of this data sheet.

#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 16 of this data sheet.

#### **DEVICE INFORMATION**

		Output V	oltage		Operating Ambient Temperature Range	
Package	3.0 V	3.3 V	5.0 V	Adjustable		
	LP2950ACZ-3.0G	LP2950ACZ-3.3G	LP2950ACZ-5.0G			
	LP2950ACZ-3.0RAG	LP2950ACZ-3.3RAG	LP2950ACZ-5.0RAG			
TO-92 Suffix Z	LP2950CZ-3.0G	LP2950CZ-3.3G	LP2950CZ-5.0G	Not Available	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	
	L D005007 0 0DAC	L D005007, 0 0DAC	LP2950CZ-5.0RAG			
	LP2950CZ-3.0RAG	LP2950CZ-3.3RAG	LP2950CZ-5.0RPG			
		LP2950ACDT-3.3RG	LP2950ACDT-5.0G		T 40° to 1125°C	
DPAK	LP2950CDT-3.0RKG	LP2950CDT-3.3G	LP2950ACDT-5RKG	Not A. allahla		
Suffix DT		LP2950CDT-3.3RKG	LP2950CDT-5.0G	Not Available	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	
			LP2950CDT-5.0RKG			
	LP2951ACD-3.0R2G	LP2951ACD-3.3R2G	LP2951ACDR2G	LP2951ACDR2G		
SOIC-8		LP2951CD-3.3R2G	LP2951CDR2G	LP2951CDR2G	T 400 to 11050C	
Suffix D	LP2951CD-3.0R2G	NCV2951ACD-3.3R2G*	NCV2951ACDR2G*	NCV2951ACDR2G*	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	
		NCV295TACD=3.3R2G"	NCV2951CDR2G*	NCV2951CDR2G*		
Micro8 Suffix DM			LP2951ACDMR2G	LP2951ACDMR2G		
	LP2951ACDM-3.0RG	LP2951ACDM-3.3RG	LP2951CDMR2G	LP2951CDMR2G	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$	
			NCV2951ACDMR2G*	NCV2951ACDMR2G*	1	

<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

 $LP2950Cx-xx \ / \ LP2951Cxx-xx \ / \ NCV2951Cx-xx \ 1\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ LP2951ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ LP2951ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ LP2950ACx-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ DCX-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ DCX-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ DCX-xx \ / \ NCV2951Ax-xx \ 0.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ DCX-xx \ / \ NCV2951Ax-xx \ O.5\% \ Output \ Voltage \ Precision \ at \ T_A = 25^{\circ}C \ DCX-xx \ / \ NCV2951Ax-xx \ O.5\% \ Output \ Voltage \ Precision \ Ax \ O.5\% \ Output \ Voltage \ Precision \ Ax \ O.5\% \ Output \ O.5\% \ O.5\% \ Output \ O.5\% \$ 

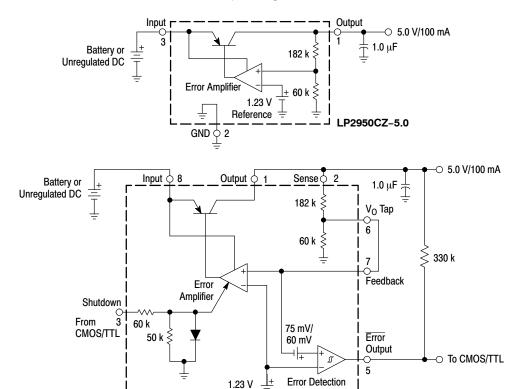


Figure 1. Representative Block Diagrams

Reference

GND  $\diamondsuit$  4

Comparator

LP2951CD or CN

This device contains 34 active transistors.

### **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ , unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage	V <sub>CC</sub>	30	Vdc
Peak Transient Input Voltage (t < 300 ms)	V <sub>CC</sub>	32	Vdc
Power Dissipation and Thermal Characteristics			
Maximum Power Dissipation	$P_{D}$	Internally Limited	W
Case 751 (SOIC-8) D Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	180	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	45	°C/W
Case 369A (DPAK) DT Suffix (Note 1)			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	92	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	6.0	°C/W
Case 29 (TO-226AA/TO-92) Z Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	160	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	83	°C/W
Case 626 N Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	105	°C/W
Case 846A (Micro8) DM Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	240	°C/W
Feedback Input Voltage	$V_{fb}$	-1.5 to +30	Vdc
Shutdown Input Voltage	$V_{sd}$	-0.3 to +30	Vdc
Error Comparator Output Voltage	V <sub>err</sub>	-0.3 to +30	Vdc
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to +125	°C
Maximum Die Junction Temperature Range	TJ	+150	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{in} = V_O + 1.0 \text{ V}, I_O = 100 \mu\text{A}, C_O = 1.0 \mu\text{F}, T_A = 25^{\circ}\text{C}$  [Note 3], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage, 5.0 V Versions	Vo				V
$V_{in} = 6.0 \text{ V}, I_O = 100 \mu\text{A}, T_A = 25^{\circ}\text{C}$					
LP2950C-5.0/LP2951C/NCV2951C*		4.950	5.000	5.050	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.975	5.000	5.025	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-5.0/LP2951C/NCV2951C*		4.900	_	5.100	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.940	_	5.060	
$V_{in}$ = 6.0 to 30 V, $I_{O}$ = 100 $\mu A$ to 100 mA, $T_{A}$ = -40 to +125°C					
LP2950C-5.0/LP2951C/NCV2951C*		4.880	_	5.120	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.925	_	5.075	
Output Voltage, 3.3 V Versions	Vo				V
$V_{in}$ = 4.3 V, $I_{O}$ = 100 $\mu A$ , $T_{A}$ = 25°C					
LP2950C-3.3/LP2951C-3.3		3.267	3.300	3.333	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.284	3.300	3.317	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-3.3/LP2951C-3.3		3.234	_	3.366	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.260	_	3.340	
$V_{in}$ = 4.3 to 30 V, $I_{O}$ = 100 $\mu A$ to 100 mA, $T_{A}$ = -40 to +125 $^{\circ} C$					
LP2950C-3.3/LP2951C-3.3		3.221	_	3.379	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.254	_	3.346	
Output Voltage, 3.0 V Versions	V <sub>O</sub>				V
$V_{in} = 4.0 \text{ V}, I_O = 100 \mu\text{A}, T_A = 25^{\circ}\text{C}$					
LP2950C-3.0/LP2951C-3.0		2.970	3.000	3.030	
LP2950AC-3.0/LP2951AC-3.0		2.985	3.000	3.015	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-3.0/LP2951C-3.0		2.940	_	3.060	
LP2950AC-3.0/LP2951AC-3.0		2.964	_	3.036	
$V_{in}$ = 4.0 to 30 V, $I_O$ = 100 $\mu A$ to 100 mA, $T_A$ = $-40$ to $+125^{\circ}C$					
LP2950C-3.0/LP2951C-3.0		2.928	_	3.072	
LP2950AC-3.0/LP2951AC-3.0		2.958	_	3.042	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 1. The Junction-to-Ambient Thermal Resistance is determined by PCB copper area per Figure 29.
- This device series contains ESD protection and exceeds the following tests: Human Body Model (HBM), 2000 V, Class 2, JESD22 A114–C Machine Model (MM), 200 V, Class B, JESD22 A115–A

Charged Device Model (CDM), 2000 V, Class IV, JESD22 C101-C

- 3. Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
- 4. V<sub>O(nom)</sub> is the part number voltage option.
- 5. Noise tests on the LP2951 are made with a 0.01 μF capacitor connected across Pins 7 and 1.
- 6. Latch-up Current Maximum Rating tested per JEDEC standard: JESD78
  - Inputs Low: passing positive current 100 mA and negative current –100 mA
  - Inputs High: passing positive current 100 mA and negative current -10 mA.

\*NCV prefix is for automotive and other applications requiring site and change control.

#### **ELECTRICAL CHARACTERISTICS** (continued)

(V<sub>in</sub> = V<sub>O</sub> + 1.0 V, I<sub>O</sub> = 100  $\mu$ A, C<sub>O</sub> = 1.0  $\mu$ F, T<sub>A</sub> = 25  $^{\circ}$ C [Note 9], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Line Regulation (V <sub>in</sub> = V <sub>O(nom)</sub> +1.0 V to 30 V) (Note 10)	Reg <sub>line</sub>				%
LP2950C-XX/LP2951C/LP2951C-XX/NCV2951C*		-	0.08	0.20	
LP2950AC-XX/LP2951AC/LP2951AC-XX/NCV2951AC*		-	0.04	0.10	21
Load Regulation (I <sub>O</sub> = 100 μA to 100 mA) LP2950C–XX/LP2951C/LP2951C–XX/NCV2951C*	Reg <sub>load</sub>	_	0.13	0.20	%
LP2950AC-XX/LP2951AC/LP2951AC-XX/NCV2951AC*		_	0.05	0.10	
Dropout Voltage	V <sub>I</sub> – V <sub>O</sub>				mV
I <sub>O</sub> = 100 μA		-	30	80	
I <sub>O</sub> = 100 mA		-	350	450	
Supply Bias Current	I <sub>CC</sub>				
$I_O = 100 \mu A$ $I_O = 100 mA$		_	93 4.0	120 12	μA mA
Dropout Supply Bias Current (V <sub>in</sub> = V <sub>O(nom)</sub> – 0.5 V,	laa	_	110	170	μΑ
$I_O = 100 \mu A$ ) (Note 10)	I <sub>CCdropout</sub>	_	110	170	μΑ
Current Limit (VO Shorted to Ground)	I <sub>Limit</sub>	_	220	300	mA
Thermal Regulation	Reg <sub>thermal</sub>	_	0.05	0.20	%/W
Output Noise Voltage (10 Hz to 100 kHz) (Note 11)	V <sub>n</sub>				μVrms
$C_L = 1.0 \mu F$		-	126	-	
C <sub>L</sub> = 100 μF		-	56	-	
LP2951A/LP2951AC Only	•	1			
Reference Voltage (T <sub>A</sub> = 25°C)	$V_{ref}$	1.010	1.005	1.000	V
LP2951C/LP2951C-XX/NCV2951C* LP2951AC/LP2951AC-XX/NCV2951AC*		1.210 1.220	1.235 1.235	1.260 1.250	
Reference Voltage (T <sub>A</sub> = -40 to +125°C)	V <sub>ref</sub>	1.220	1.200	1.200	V
LP2951C/LP2951C-XX/NCV2951C*	- 161	1.200	-	1.270	•
LP2951AC/LP2951AC-XX/NCV2951AC*		1.200	_	1.260	
Reference Voltage ( $T_A = -40 \text{ to } +125^{\circ}\text{C}$ )	$V_{ref}$				V
I <sub>O</sub> = 100 μA to 100 mA, V <sub>in</sub> = 23 to 30 V LP2951C/LP2951C-XX/NCV2951C*		4.405		4 005	
LP29516/LP29516-XX/NCV29516" LP2951AC/LP2951AC-XX/NCV2951AC*		1.185 1.190	_	1.285 1.270	
Feedback Pin Bias Current	I <sub>FB</sub>	-	15	40	nA
Error Comparator	l.	1		1	1
Output Leakage Current (V <sub>OH</sub> = 30 V)	I <sub>lkg</sub>	_	0.01	1.0	μΑ
Output Low Voltage (V <sub>in</sub> = 4.5 V, I <sub>OL</sub> = 400 μA)	V <sub>OL</sub>	-	150	250	mV
Upper Threshold Voltage (V <sub>in</sub> = 6.0 V)	$V_{thu}$	40	45	-	mV
Lower Threshold Voltage (V <sub>in</sub> = 6.0 V)	$V_{thl}$	-	60	95	mV
Hysteresis (V <sub>in</sub> = 6.0 V)	$V_{hy}$	=	15	-	mV
Shutdown Input					
Input Logic Voltage	V <sub>shtdn</sub>				V
Logic "0" (Regulator "On")		0	-	0.7	
Logic "1" (Regulator "Off")		2.0	_	30	
Shutdown Pin Input Current $V_{shtdn} = 2.4 \text{ V}$	l <sub>shtdn</sub>	_	35	50	μΑ
V <sub>shtdn</sub> = 30 V		_	450	600	
Regulator Output Current in Shutdown Mode	I <sub>off</sub>	-	3.0	10	μΑ
$(V_{in} = 30 \text{ V}, V_{shtdn} = 2.0 \text{ V}, V_{O} = 0, \text{Pin 6 Connected to Pin 7})$					

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>7.</sup> The Junction-to-Ambient Thermal Resistance is determined by PCB copper area per Figure 29.

<sup>8.</sup> ESD data available upon request.

<sup>9.</sup> Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

<sup>10.</sup>  $V_{O(nom)}$  is the part number voltage option. 11. Noise tests on the LP2951 are made with a 0.01  $\mu$ F capacitor connected across Pins 7 and 1.

<sup>\*</sup>NCV prefix is for automotive and other applications requiring site and change control.

#### **DEFINITIONS**

**Dropout Voltage** – The input/output voltage differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output drops 100 mV below its nominal value (which is measured at 1.0 V differential), dropout voltage is affected by junction temperature, load current and minimum input supply requirements.

**Line Regulation** – The change in output voltage for a change in input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that average chip temperature is not significantly affected.

**Load Regulation** – The change in output voltage for a change in load current at constant chip temperature.

**Maximum Power Dissipation** – The maximum total device dissipation for which the regulator will operate within specifications.

**Bias Current** – Current which is used to operate the regulator chip and is not delivered to the load.

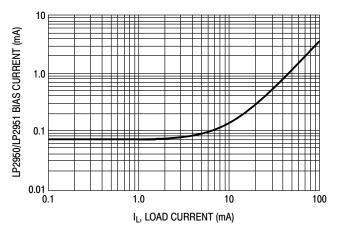


Figure 2. Quiescent Current

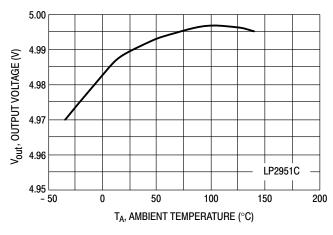


Figure 4. Output Voltage versus Temperature

**Output Noise Voltage** – The RMS ac voltage at the output, with constant load and no input ripple, measured over a specified frequency range.

**Leakage Current** – Current drawn through a bipolar transistor collector–base junction, under a specified collector voltage, when the transistor is "off".

**Upper Threshold Voltage** – Voltage applied to the comparator input terminal, below the reference voltage which is applied to the other comparator input terminal, which causes the comparator output to change state from a logic "0" to "1".

**Lower Threshold Voltage** – Voltage applied to the comparator input terminal, below the reference voltage which is applied to the other comparator input terminal, which causes the comparator output to change state from a logic "1" to "0".

**Hysteresis** – The difference between Lower Threshold voltage and Upper Threshold voltage.

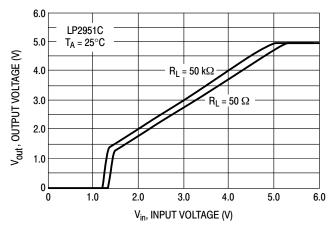


Figure 3. 5.0 V Dropout Characteristics over Load

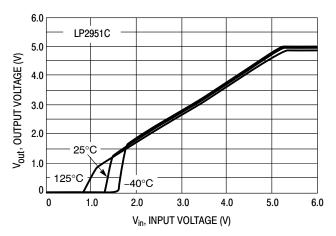


Figure 5. 5.0 V Dropout Characteristics with  $\mbox{R}_L$  = 50  $\Omega$ 

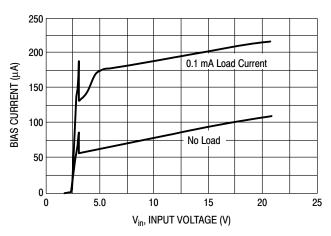


Figure 6. Input Current

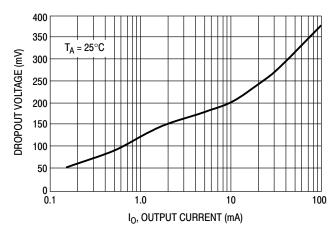


Figure 7. Dropout Voltage versus Output Current

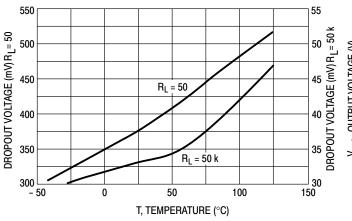


Figure 8. Dropout Voltage versus Temperature

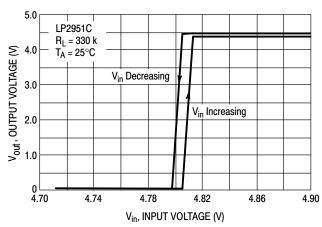


Figure 9. Error Comparator Output

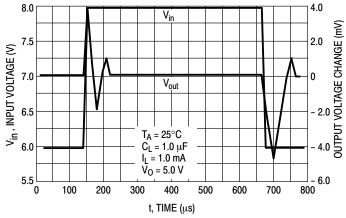


Figure 10. Line Transient Response

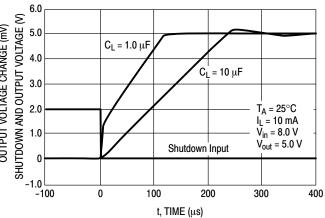


Figure 11. LP2951 Enable Transient

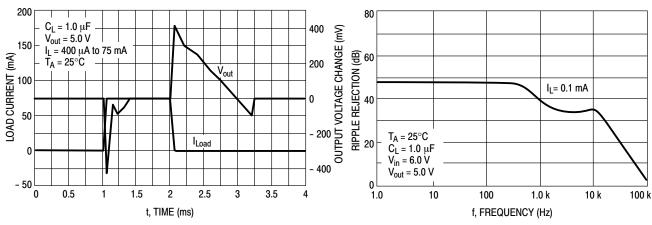


Figure 12. Load Transient Response

Figure 13. Ripple Rejection

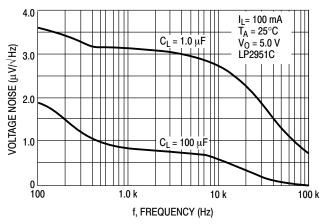


Figure 14. Output Noise

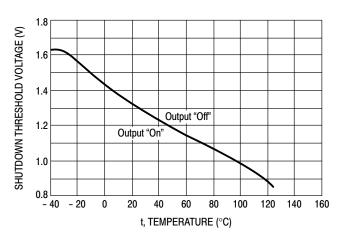


Figure 15. Shutdown Threshold Voltage versus Temperature

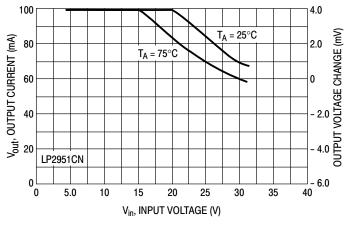


Figure 16. Maximum Rated Output Current

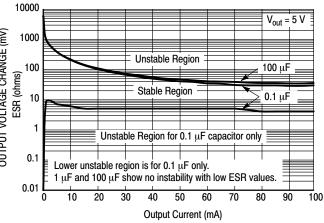


Figure 17. Output Stability versus Output Capacitor Change

#### **APPLICATIONS INFORMATION**

#### Introduction

The LP2950/LP2951 regulators are designed with internal current limiting and thermal shutdown making them user-friendly. Typical application circuits for the LP2950 and LP2951 are shown in Figures 20 through 28.

These regulators are not internally compensated and thus require a 1.0  $\mu F$  (or greater) capacitance between the LP2950/LP2951 output terminal and ground for stability. Most types of aluminum, tantalum or multilayer ceramic will perform adequately. Solid tantalums or appropriate multilayer ceramic capacitors are recommended for operation below  $25^{\circ} C.$ 

At lower values of output current, less output capacitance is required for output stability. The capacitor can be reduced to  $0.33~\mu F$  for currents less than 10~mA, or  $0.1~\mu F$  for currents below 1.0~mA. Using the 8 pin versions at voltages less than 5.0~V operates the error amplifier at lower values of gain, so that more output capacitance is needed for stability. For the worst case operating condition of a 100~mA load at 1.23~V output (output Pin 1 connected to the feedback Pin 7) a minimum capacitance of  $3.3~\mu F$  is recommended.

The LP2950 will remain stable and in regulation when operated with no output load. When setting the output voltage of the LP2951 with external resistors, the resistance values should be chosen to draw a minimum of  $1.0~\mu A$ .

A bypass capacitor is recommended across the LP2950/LP2951 input to ground if more than 4 inches of wire connects the input to either a battery or power supply filter capacitor.

Input capacitance at the LP2951 Feedback Pin 7 can create a pole, causing instability if high value external resistors are used to set the output voltage. Adding a 100 pF capacitor between the Output Pin 1 and the Feedback Pin 7 and increasing the output filter capacitor to at least 3.3  $\mu F$  will stabilize the feedback loop.

#### **Error Detection Comparator**

The comparator switches to a positive logic low whenever the LP2951 output voltage falls more than approximately 5.0% out of regulation. This value is the comparator's designed–in offset voltage of 60 mV divided by the 1.235 V internal reference. As shown in the representative block diagram. This trip level remains 5.0% below normal regardless of the value of regulated output voltage. For example, the error flag trip level is 4.75 V for a normal 5.0 V regulated output, or 9.50 V for a 10 V output voltage.

Figure 2 is a timing diagram which shows the  $\overline{ERROR}$  signal and the regulated output voltage as the input voltage

to the LP2951 is ramped up and down. The ERROR signal becomes valid (low) at about 1.3 V input. It goes high when the input reaches about 5.0 V (Vout exceeds about 4.75 V). Since the LP2951's dropout voltage is dependent upon the load current (refer to the curve in the Typical Performance Characteristics), the input voltage trip point will vary with load current. The output voltage trip point does not vary with load.

The error comparator output is an open collector which requires an external pullup resistor. This resistor may be returned to the output or some other voltage within the system. The resistance value should be chosen to be consistent with the 400  $\mu A$  sink capability of the error comparator. A value between 100 k $\Omega$  and 1.0 M $\Omega$  is suggested. No pullup resistance is required if this output is unused.

When operated in the power down mode ( $V_{in}$  = 0 V), the error comparator output will go high if it has been pulled up to an external supply (the output transistor is in high impedance state). To avoid this invalid response, the error comparator output should be pulled up to  $V_{out}$  (see Figure 18).

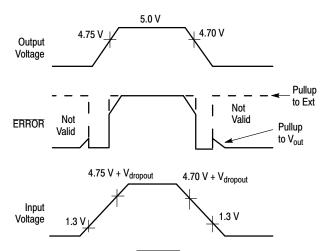


Figure 18. ERROR Output Timing

#### **Programming the Output Voltage (LP2951)**

The LP2951CX may be pin-strapped for the nominal fixed output voltage using its internal voltage divider by tying Pin 1 (output) to Pin 2 (sense) and Pin 7 (feedback) to Pin 6 (5.0 V tap). Alternatively, it may be programmed for any output voltage between its 1.235 reference voltage and its 30 V maximum rating. An external pair of resistors is required, as shown in Figure 19.

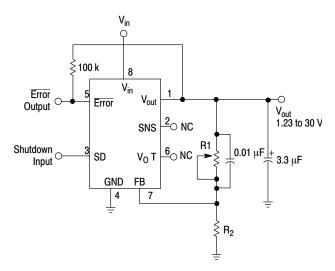


Figure 19. Adjustable Regulator

The complete equation for the output voltage is:

$$V_{out} = V_{ref} (1 + R1/R2) + I_{FB} R1$$

where  $V_{ref}$  is the nominal 1.235 V reference voltage and  $I_{FB}$  is the feedback pin bias current, nominally -20 nA. The minimum recommended load current of 1.0  $\mu A$  forces an upper limit of 1.2 M $\Omega$  on the value of R2, if the regulator must work with no load.  $I_{FB}$  will produce a 2% typical error in  $V_{out}$  which may be eliminated at room temperature by adjusting R1. For better accuracy, choosing R2 = 100 k reduces this error to 0.17% while increasing the resistor program current to 12  $\mu A$ . Since the LP2951 typically draws 75  $\mu A$  at no load with Pin 2 open circuited, the extra 12  $\mu A$  of current drawn is often a worthwhile tradeoff for eliminating the need to set output voltage in test.

#### **Output Noise**

In many applications it is desirable to reduce the noise present at the output. Reducing the regulator bandwidth by increasing the size of the output capacitor is the only method for reducing noise on the 3 lead LP2950. However, increasing the capacitor from 1.0  $\mu F$  to 220  $\mu F$  only decreases the noise from 430  $\mu V$  to 160  $\mu V rms$  for a 100 kHz bandwidth at the 5.0 V output.

Noise can be reduced fourfold by a bypass capacitor across R1, since it reduces the high frequency gain from 4 to unity. Pick

$$C_{Bypass} \approx \frac{1}{2\pi R1 \times 200 \text{ Hz}}$$

or about 0.01  $\mu$ F. When doing this, the output capacitor must be increased to 3.3  $\mu$ F to maintain stability. These changes reduce the output noise from 430  $\mu$ V to 126  $\mu$ Vrms for a 100 kHz bandwidth at 5.0 V output. With bypass capacitor added, noise no longer scales with output voltage so that improvements are more dramatic at higher output voltages.

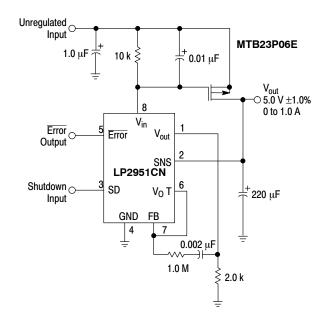


Figure 20. 1.0 A Regulator with 1.2 V Dropout

#### **TYPICAL APPLICATIONS**

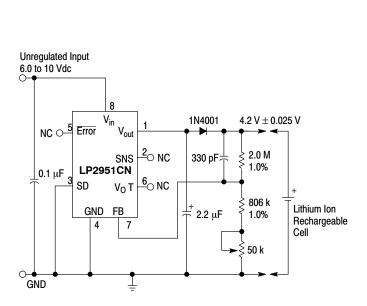


Figure 21. Lithium Ion Battery Cell Charger

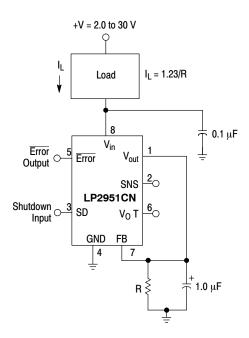


Figure 22. Low Drift Current Sink

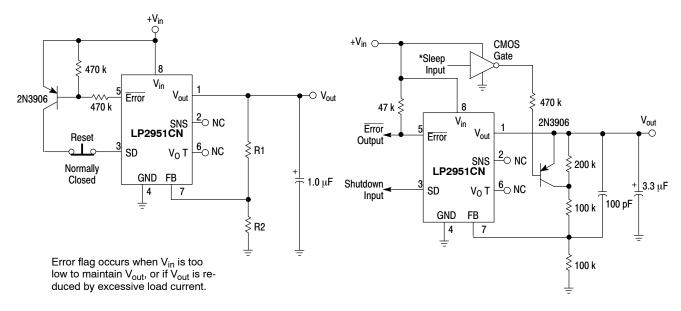
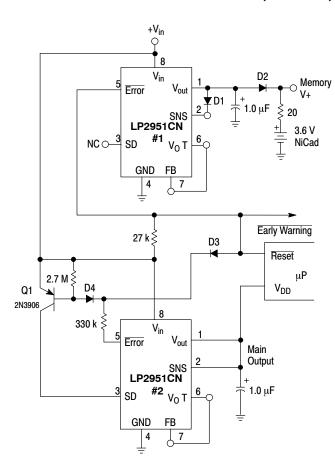


Figure 23. Latch Off When Error Flag Occurs

Figure 24. 5.0 V Regulator with 2.5 V Sleep Function



All diodes are 1N4148.

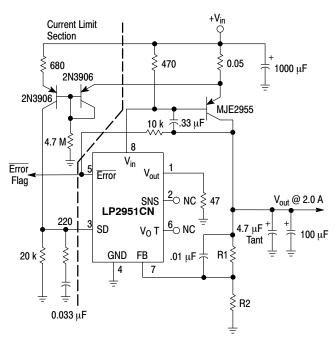
Early Warning flag on low input voltage.

Main output latches off at lower input voltages.

Battery backup on auxiliary output.

Operation: Regulator #1's  $V_{out}$  is programmed one diode drop above 5.0 V. Its error flag becomes active when  $V_{in} \leq 5.7$  V. When  $V_{in}$  drops below 5.3 V, the error flag of regulator #2 becomes active and via Q1 latches the main output "off". When  $V_{in}$  again exceeds 5.7 V, regulator #1 is back in regulation and the early warning signal rises, unlatching regulator #2 via D3.

Figure 25. Regulator with Early Warning and Auxiliary Output



 $V_{out} = 1.25V (1.0 + R1/R2)$ 

For 5.0 V output, use internal resistors. Wire Pin 6 to 7, and wire Pin 2 to +V  $_{out}$  Bus.

Figure 26. 2.0 A Low Dropout Regulator

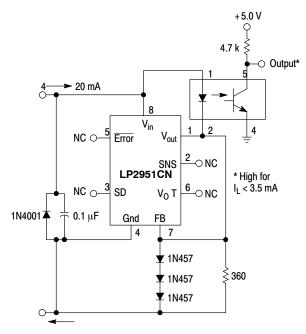


Figure 27. Open Circuit Detector for 4.0 to 20 mA Current Loop

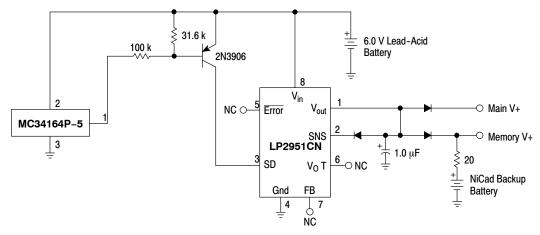


Figure 28. Low Battery Disconnect

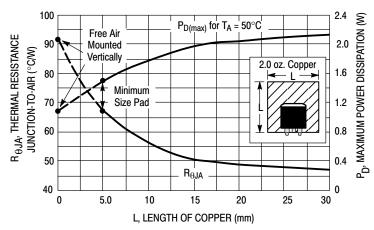


Figure 29. DPAK Thermal Resistance and Maximum Power Dissipation versus PCB Copper Length

#### **ORDERING INFORMATION (LP2950)**

Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
LP2950CZ-3.0G	3.0	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-3.0RAG	3.0	1.0	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950ACZ-3.0G	3.0	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-3.0RAG	3.0	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-3.3G	3.3	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-3.3RAG	3.3	1.0	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950ACZ-3.3G	3.3	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-3.3RAG	3.3	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-5.0G	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-5.0RAG	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-5.0RPG	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Ammo Pack
LP2950ACZ-5.0G	5.0	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-5.0RAG	5.0	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CDT-3.0RKG	3.0	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950CDT-3.3G	3.3	1.0	DPAK (Pb-Free)	75 Units / Rail
LP2950CDT-3.3RKG	3.3	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950ACDT-3.3RG	3.3	0.5	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950CDT-5.0G	5.0	1.0	DPAK (Pb-Free)	75 Units / Rail
LP2950CDT-5.0RKG	5.0	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950ACDT-5.0G	5.0	0.5	DPAK (Pb-Free)	75 Units / Rail
LP2950ACDT-5RKG	5.0	0.5	DPAK (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ORDERING INFORMATION (LP2951)**

Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
LP2951CD-3.0R2G	3.0	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACD-3.0R2G	3.0	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951CD-3.3R2G	3.3	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACD-3.3G	3.3	0.5	SOIC-8 (Pb-Free)	98 Units / Rail
LP2951ACD-3.3R2G	3.3	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951CDG	5.0 or Adj.	1.0	SOIC-8 (Pb-Free)	98 Units / Rail
LP2951CDR2G	5.0 or Adj.	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACDG	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	98 Units / Rail
LP2951ACDR2G	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACDM-3.0RG	-3.0RG 3.0 0.		Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951ACDM-3.3RG	3.3	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951CDMR2G	5.0 or Adj.	1.0	Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951ACDMR2G	5.0 or Adj.	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

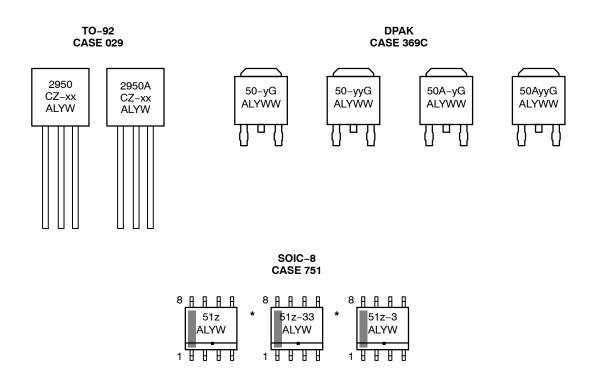
#### **ORDERING INFORMATION (NCV2951)**

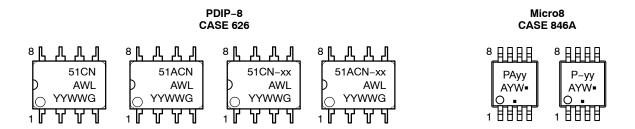
Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
NCV2951ACD3.3R2G*	3.3	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951ACDR2G*	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951CDR2G*	5.0 or Adj.	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951ACDMR2G*	5.0 or Adj.	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

#### **MARKING DIAGRAMS**





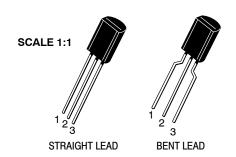
xx = 3.0, 3.3, or 5.0 y = 3 or 5 yy = 30, 33, or 50 z = A or C

A = Assembly Location WL, L = Wafer Lot

YY, Y = Year WW, W = Work Week G = Pb−Free Package ■ Pb−Free Package

(Note: Microdot may be in either location)

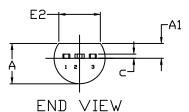
<sup>\*</sup>This marking diagram also applies to NCV2951.

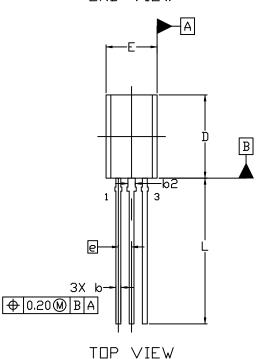


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### STRAIGHT LEAD





#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS						
DIM	MIN.	N□M.	MAX.				
Δ	3.75	3.90	4.05				
A1	1.28	1.43	1.58				
Ø	0.38	0.465	0.55				
ρQ	0.62	0.70	0.78				
C	0.35	0.40	0.45				
D	7.85	8.00	8.15				
E	4.75	4.90	5.05				
E2	3.90						
е	1.27 BSC						
L	13.80 14.00 14.20						

#### **STYLES AND MARKING ON PAGE 3**

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DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 1 OF 3			

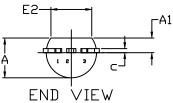
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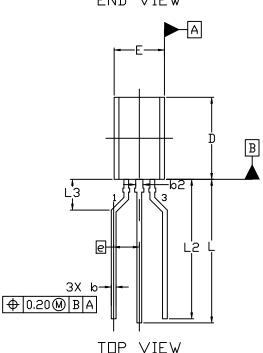


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

#### FORMED LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Α	3.75	3.90	4.05			
A1	1.28	1.43	1.58			
b	0.38	0.465	0.55			
b2	0.62	0.70	0.78			
С	0.35	0.40	0.45			
D	7.85	8.00	8.15			
Е	4.75 4.90		5.05			
E2	3.90					
е	2.50 BSC					
L	13.80	14.00	14.20			
L2	13.20	13.60	14.00			
L3	3.00 REF					

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#### TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

#### **DATE 05 MAR 2021**

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE		DRAIN
	GATE	PIN 1.	SOURCE DRAIN			PIN 1. 2.	BASE 1 EMITTER BASE 2	2.	CATHODE GATE ANODE
2.	ANODE CATHODE & ANODE	PIN 1. 2.	GATE	PIN 1. 2.	ANODE 1	2.	EMITTER COLLECTOR BASE		
2.	ANODE	PIN 1		PIN 1	ANODE	PIN 1. 2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.			SOURCE GATE	STYLE 23: PIN 1. 2. 3.	GATE	PIN 1. 2.		PIN 1. 2.	MT 1
	V <sub>CC</sub>	PIN 1. 2.	MT	STYLE 28: PIN 1. 2. 3.	CATHODE	PIN 1. 2.	NOT CONNECTED ANODE CATHODE		
	GATE	PIN 1. 2.		STYLE 33: PIN 1. 2. 3.	RETURN	2.	INPUT GROUND LOGIC		

# GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

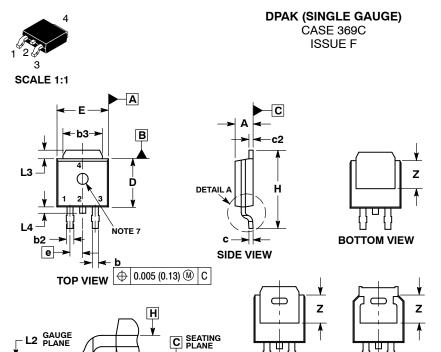
(Note: Microdot may be in either location)

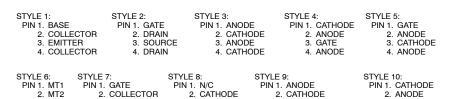
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 3 OF 3

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3. ANODE 4. CATHODE

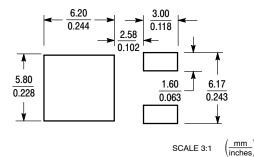
#### **SOLDERING FOOTPRINT\***

Α1

3. EMITTER 4. COLLECTOR

**DETAIL A** ROTATED 90° CW

3. GATE 4. MT2



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# onsemi

**DATE 21 JUL 2015** 

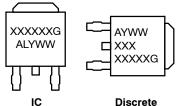
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

#### **GENERIC MARKING DIAGRAM\***



XXXXXX = Device Code = Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

**BOTTOM VIEW** 

ALTERNATE CONSTRUCTIONS

3. RESISTOR ADJUST 4. CATHODE

3. CATHODE 4. ANODE

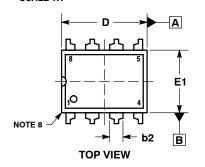
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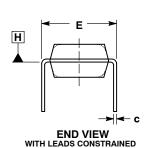


PDIP-8 CASE 626-05 ISSUE P

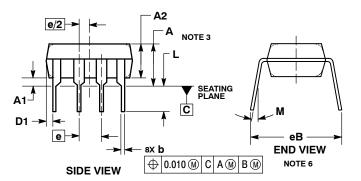
**DATE 22 APR 2015** 







NOTE 5



STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN

- 5. GROUND 6. OUTPUT
- 7. AUXILIARY 8. V<sub>CC</sub>

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- 8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100 BSC		2.54	BSC
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	PDIP-8		PAGE 1 OF 1

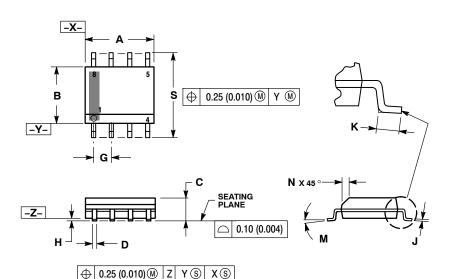
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SOIC-8 NB CASE 751-07 **ISSUE AK** 

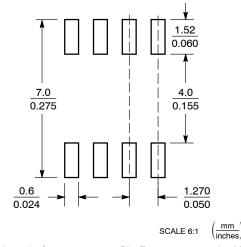
**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

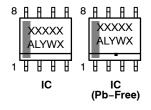
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
7	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

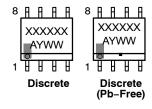
#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year W

ww = Work Week = Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### **DATE 16 FEB 2011**

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	PIN 1. INPUT  2. EXTERNAL BYPASS  3. THIRD STAGE SOURCE  4. GROUND  5. DRAIN  6. GATE 3  7. SECOND STAGE Vd  8. FIRST STAGE Vd	PIN 1. COLLECTOR, DIE #1 2. BASE, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 9. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN
3. V10UT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC  STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22:	7. DRAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

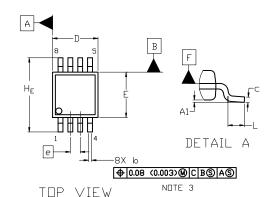
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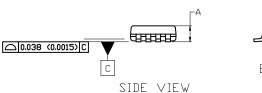
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#### Micro8 CASE 846A-02 ISSUE K

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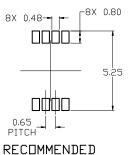




END VIEW

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



MOUNTING FOOTPRINT

DIM	MI	LLIMETE	RS
ויונע	MIN.	N□M.	MAX.
Α	-	-	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
Ε	2.90	3.00	3.10
е	0.65 BSC		
HE	4.75	4.90	5.05
L	0.40	0.55	0.70

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
<ol><li>SOURCE</li></ol>	2. GATE 1	2. N-GATE
<ol><li>SOURCE</li></ol>	3. SOURCE 2	3. P-SOURCE
<ol><li>GATE</li></ol>	4. GATE 2	4. P-GATE
<ol><li>DRAIN</li></ol>	5. DRAIN 2	5. P-DRAIN
<ol><li>DRAIN</li></ol>	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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